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" mining		A GUES IN IMPENETOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	JP920000112US1	8744
	05/15/2001	Takatoshi Tsujimura		
x 77 7	RATION, T.J. WATSON RESEARCH CENTER		EXAMINER	
n o nov 218			COLEMAN, V	WILLIAM D
YORKTOWN	HEIGHTS, NY 10598		ART UNIT	PAPER NUMBER
			2823	9
			DATE MAILED: 02/04/2003	<i>'</i>

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)	
	09/681,643	TSUJIMURA ET AL.	
Office Action Summary	Examiner	Art Unit	
	W. David Coleman	2823	
The MAILING DATE of this communication a	appears on the cover she	eet with the correspondence address	
and for Donly			
A SHORTENED STATUTORY PERIOD FOR REI THE MAILING DATE OF THIS COMMUNICATIO Extensions of time may be available under the provisions of 37 CFR after SIX (6) MONTHS from the mailing date of this communication If the period for reply specified above is less than thirty (30) days, a If NO period for reply is specified above, the maximum statutory per Failure to reply within the set or extended period for reply will, by standard to the second of the second of the maximum statutory per Any reply received by the Office later than three months after the meanned patent term adjustment. See 37 CFR 1.704(b).	R 1.136(a). In no event, however, in a reply within the statutory minimum eriod will apply and will expire SIX (to the statutory minimum eriod will apply and will expire SIX (to the statutory minimum eriod will apply and will expire SIX (to the statutory minimum eriod will apply and will expire SIX (to the statutory minimum eriod will apply and will expire SIX (to the statutory minimum eriod will apply and will expire statutory minimum eriod will apply and will expire statutory minimum eriod.	may a reply be timely filed m of thirty (30) days will be considered timely (6) MONTHS from the mailing date of this communication	
Status	04 December 2002		
1) Responsive to communication(s) filed on	This action is non-final	i.	
Za) This action is the interest of the interes	The second of th		
3) Since this application is in condition for all closed in accordance with the practice un	nder Ex parte Quayle, 19	935 C.D. 11, 453 O.G. 213.	
Disposition of Claims			
A) Claim(s) 1-16 is/are pending in the applica	ation.		
4a) Of the above claim(s) 10-16 is/are with	ndrawn from consideratic	on.	
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>1-9</u> is/are rejected.			
7) Claim(s) is/are objected to.			
8) Claim(s) are subject to restriction a	and/or election requirem	ent.	
Application Papers			
The exception is objected to by the Exa	aminer. —	Les by the Everniner	
is/are: a)] accepted or b)∐_ objected	g to by the Examine.	
that any objection	in to the drawing(s) be neld	In abeyance. See or or it has the	
11) The proposed drawing correction filed on	is: a) approved	d b) disapproved by the Examiner	
If approved, corrected drawings are required	ed in reply to this Office action	on.	
12)☐ The oath or declaration is objected to by t	tne Examiner.		
		1100 8 140/a) (d) ar (f)	
13) Acknowledgment is made of a claim for f	foreign priority under 35	1 U.S.C. 8 1 18(8)-(a) 01 (1).	
a)☐ All b)☐ Some * c)☐ None of:			
A Contified copies of the priority doct	uments have been recei	ived.	
viting anning of the priority doci	cuments have been recei	eived in Application No	
3. Copies of the certified copies of the application from the Internation	he priority documents ha onal Bureau (PCT Rule 1 or a list of the certified co	ave been received in this National Stage 17.2(a)). Opies not received.	
* See the attached detailed Office action to 14) Acknowledgment is made of a claim for d	omestic priority under 35	5 U.S.C. § 119(e) (to a provisional application).	
su to a longue	iaga provisional application	ION Has been received.	
15) Acknowledgment is made of a claim for c	domestic priority under \$	35 U.S.C. §§ 120 and/or 121.	
Attachment(s)	4) 🗌	Interview Summary (PTO-413) Paper No(s).	
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-3) Information Disclosure Statement(s) (PTO-1449) Paper)-948) 5) 🔲	5 Application (PTO-152)	
3) [Information Disclosure Statement(5) (1.2.7.7.7.7.7.7.7.7.7.7.7.7.7.7.7.7.7.7.		Part of Paner No. 9	

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DETAILED ACTION

Election/Restrictions

1. Applicant's election with traverse of claims 1-10 in Paper No. 8 is acknowledged. The traversal is on the ground(s) that claims 10-16 are not classifiable in class 118. This is not found persuasive because as Applicant has stated to be classified in this class the work treated must not be a part of the coating machine itself but must be an article separate and distinct therefrom. It is well known that semiconductor devices fabricated in process chambers are not part of the coating machine and therefore the restriction requirement was proper.

2. The requirement is still deemed proper and is therefore made FINAL.

Response to Arguments

- 3. Applicant's arguments filed December 4, 2002 have been fully considered but they are not persuasive.
- 4. Applicants contend that the current patent application filed May 15, 2001 is entitled to the benefits of having the present application examined under the AIPA changes to 35 U.S.C. 102 § 102(e).
- 5. In response to Applicants contention that the current Application was examined under 35 U.S.C. 102 § 102(e), Applicants are mistaken. The present Application was rejected under 35 U.S.C. 103(a), see MPEP 706.02(j).
- 6. In response to applicant's argument that there is no suggestion to combine the references, the examiner recognizes that obviousness can only be established by combining or modifying the teachings of the prior art to produce the claimed invention where there is some teaching,

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suggestion, or motivation to do so found either in the references themselves or in the knowledge generally available to one of ordinary skill in the art. See In re Fine, 837 F.2d 1071, 5 USPQ2d 1596 (Fed. Cir. 1988)and In re Jones, 958 F.2d 347, 21 USPQ2d 1941 (Fed. Cir. 1992). In this case, the chamber requires cleaning after the formation of the oxide layer, it is obvious that an oxide is formed on the chamber wall.

Claim Rejections - 35 USC § 103

- The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all 7. obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- Claims 1-10 are rejected under 35 U.S.C. 103(a) as being unpatentable over Ohnuma et 8. al., U.S. Patent 6,072,193 in view of Gardner et al., U.S. Patent 6,066,519.
- Pertaining to claims 1 and 2, Ohnuma discloses a semiconductor process substantially as 9. claimed. See FIGS. 1A-2D, where Ohnuma teaches a manufacturing method of an active matrix device (column 17, line 62) including a top gate type TFT, which comprises a process of forming the top gate type TFT, wherein the process of forming the top gate type TFT includes the steps of:

arranging a substrate 101 having source 125 and drain electrodes 126 formed therein in the processing chamber; doping the source and drain electrodes with P (phosphorous), (column 3, lines 51-54); and forming an a-Si layer 103 and a gate insulating film 104 in the processing chamber. However, Ohnuma fails to disclose forming an oxide film on an inner wall of a CVD processing chamber. Gardner teaches forming an oxide on an inner wall of a CVD processing

Page 4 Application/Control Number: 09/681,643 Art Unit: 2823 chamber (column 6, lines 8-14). In view of Gardner, it would have been obvious to one of ordinary skill in the art because when forming a gate dielectric residual oxide forms on the chamber walls (column 6, lines 10-12). Pertaining to claim 2, Ohnuma fails to disclose removing the oxide film form the inner 10. wall after the step of forming the a-Si layer and the gate insulating layer. Gardner teaches the step of removing oxide between runs. In view Gardner, it would have been obvious to one of ordinary skill in the are to remove oxide from the chamber walls after the step of forming the a-Si layer and the gate insulating film because the a silicon gate dielectric layer may be formed in a highly controlled manner (column 6, lines 21-23). Pertaining to claim 3, Ohnuma teaches a manufacturing method of an active matrix 11. device according to claim 1, wherein the oxide film contains SiOx. Pertaining to claim 4, Ohnuma teaches a manufacturing method of an active matrix 12. device according to claim 1, wherein the active matrix device is a liquid crystal display (column 17, line 62). Pertaining to claim 5, Ohnuma teaches a manufacturing method of an active matrix 13. device according to claim 1, wherein the active matrix device is an electroluminescence display (column 17, line 62). Pertaining to claim 6, Ohnuma teaches a manufacturing method of an active matrix 14. device according to claim 2, wherein the oxide film contains SiOx. Pertaining to claim 7, Ohnuma teaches a manufacturing method of an active matrix 15. device according to claim 2, wherein the active matrix device is a liquid crystal display.

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- 16. Pertaining to claim 8, Ohnuma teaches a manufacturing method of an active matrix device according to claim 3, wherein the active matrix device is a liquid crystal display.
- 17. Pertaining to claim 9, Ohnuma teaches a manufacturing method of an active matrix device according to claim 2, wherein the active matrix device is an electroluminescence display.
- 18. Pertaining to claim 10, <u>Ohnuma</u> teaches a manufacturing method of an active matrix device according to claim 3, wherein the active matrix device is an electroluminescence display.

Conclusion

- 19. **THIS ACTION IS MADE FINAL.** Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).
- 20. A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.
- 21. Any inquiry concerning this communication or earlier communications from the examiner should be directed to W. David Coleman whose telephone number is 703-305-0004. The examiner can normally be reached on 9:00 AM-5:00 PM.